

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company





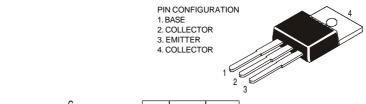


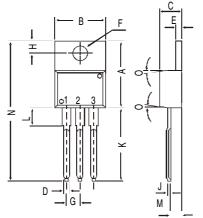
TO-220 Plastic Package

BDX53, BDX53A, BDX53B, BDX53C BDX54, BDX54A, BDX54B, BDX54C

BDX53, 53A, 53B, 53C NPN PLASTIC POWER TRANSISTORS BDX54, 54A, 54B, 54C PNP PLASTIC POWER TRANSISTORS

Power Darlingtons for Linear and Switching Applications





	DIM	MIN.	MAX.	
diminsions in mm.	Α	14.42	16.51	
	В	9.63	10.67	
	С	3.56	4.83	
	D		0.90	
	Е	1.15	1.40	
	F	3.75	3.88	
	G	2.29	2.79	
	Н	2.54	3.43	
	J		0.56	
	K	12.70	14.73	
	L	2.80	4.07	
	М	2.03	2.92	
	N		31.24	
₹	0	DEG 7		

ABSOLUTE MAXIMUM RATINGS

Collector-emitter voltage (open base)

Emitter-base voltage (open collector)

ABSOLUTE MARKINGA INTINGS									
			53	53A	53B	53 <i>C</i>			
			54	54A	54B	54C			
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	80	100	V		
Collector-emitter voltage (open base)	V_{CEO}	max.	45	60	80	100	V		
Collector current	I_C	max.		8.0			A		
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.		6	50		W		
Junction temperature	T_j	max.		150			$^{\circ}\!C$		
Collector-emitter saturation voltage	,								
$I_C = 3 A; I_B = 12 mA$	V_{CEsat}	max.		2.0			V		
D.C. current gain									
$I_C = 3 A; V_{CE} = 3 V$	h_{FE}	min.		750					
RATINGS (at T_A =25°C unless otherwise specified)									
Limiting values			53	53A	53B	53C			
			54	54A	54B	54C			
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	80	100	V		

 V_{CEO}

 V_{EBO}

max. 45

max.

60

80

5.0

V

BDX53, BDX53A, BDX53B, BDX53C BDX54, BDX54A, BDX54B, BDX54C

Collector current Collector current (Peak value) Base current Total power dissipation upto T _C =25°C Derate above 25°C	I _C I _{CM} I _B P _{tot}	max. max. max. max.	1 0. 6	.0 2 .2 0 48		$A \\ A \\ A \\ W \\ W \\ C$
Junction temperature	T_j	max.	150			°C
Storage temperature	T_{stg}^{J}		-65	5 to +	150	\mathcal{C}
THERMAL RESISTANCE	D		2	0.0		00/147
From junction to case From junction to ambient	R _{th j–c} R _{th j–a}		2.08 7.0			°Ç/W °Ç/W
•	rem j–a		, ,	.0		911
CHARACTERISTICS $T_{amb} = 25^{\circ}C$ unless otherwise specified						
1 amo – 25 C unicss onerwise specifica		53	53A	53B	53 <i>C</i>	
		54	54A	54B	54C	
Collector cutoff current	-					
$I_B = 0; V_{CB} = 45 V$	I_{CBO}	max. 0.2	-	_	-	mA
$I_B = 0; V_{CB} = 60 V$	I_{CBO}	max. –	0.2	-	-	mA
$I_B = 0; V_{CB} = 80 \text{ V}$	I _{CBO}	max	_	0.2	-	mA
$I_B = 0; V_{CB} = 100 V$	I _{CBO}	max	_	_	0.2	mA mA
$I_B = 0; V_{CE} = 22 V$ $I_B = 0; V_{CE} = 30 V$	ICEO	max. 0.5 max. –	0.5	_	_	mA
$I_B = 0$, $V_{CE} = 30 \text{ V}$ $I_B = 0$; $V_{CE} = 40 \text{ V}$	I _{CEO}	max	-	0.5	_	mA
IB = 0; $VCE = 40$ V $IB = 0$; $VCE = 50$ V	I _{CEO} I _{CEO}	max. -	_	_	0.5	mA
Emitter cut-off current	ICEU	mux.			0.0	11121
$I_C = 0; V_{EB} = 5 V$	I_{EBO}	max.	2.	.0		mA
Breakdown voltages	-LBC					
$I_C = 100 \text{ mA}; I_B = 0$	V _{CEO(sus)} *	min. 45	60	80	100	V
$I_C = 1 mA; I_E = 0$	V_{CBO}	min. 45	60	80	100	V
$I_E = 1 mA; I_C = 0$	V_{EBO}	min.	5.	.0		V
Saturation voltages						
$I_C = 3 A; I_B = 12 mA$	V_{CEsat}^*	max.		.0		V
	V_{BEsat}^*	max.	2.	.5		V
D.C. current gain		_				
$I_C = 3 A$; $V_{CE} = 3 V$	h_{FE}^*	min.	75	50		
Small signal current gain	1.7			0		
$I_C = 3 A; V_{CE} = 4 V; f = 1.0 MHz$ Output capacitance $f = 1.0 MHz$	∣h _{fe} ∣	min.	4.	.0		
$I_E = 0; V_{CB} = 10 V$ NPN	C_o	max.	30	00		рF
PNP	C_0	max.		00		рF
Parallel-diode forward voltage	-0			-		Γ-
$I_F = 3 A$	V_F	max.	2.	.5		V
$I_F = 8 A$	V_F	typ.	2.	.5		V
		- '				

^{*} Pulse test: pulse width $\leq 300~\mu s$; duty cycle $\leq 2\%$

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of
Continental Device India Limited
C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com